/ Descriptions

TO-252

Ultrafast Recovery Diode in a TO-252 Plastic Package.

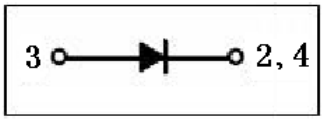
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

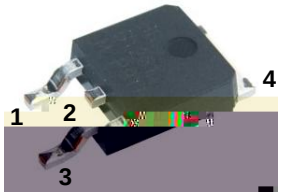
/ Applications

For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.

/ Equivalent Circuit



/ Pinning



PIN1 NC PIN 2 Cathode PIN 3 Anode PIN 4:Case

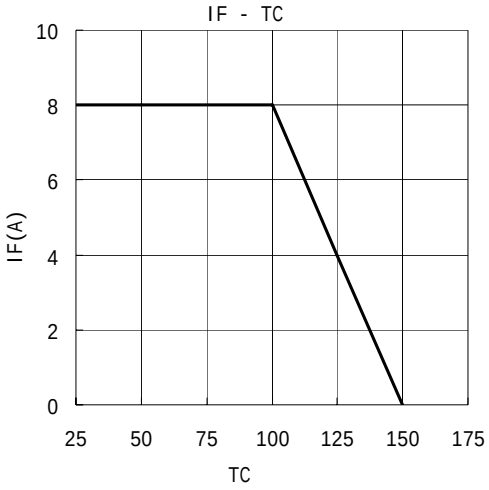
/ h_{FE} Classifications & Marking

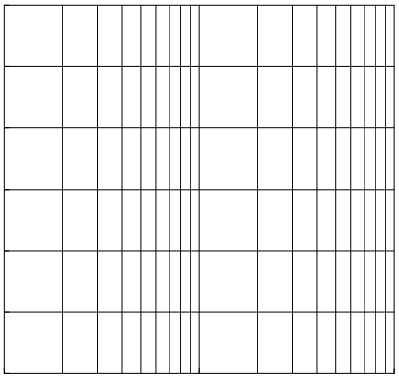
See Marking Instructions.

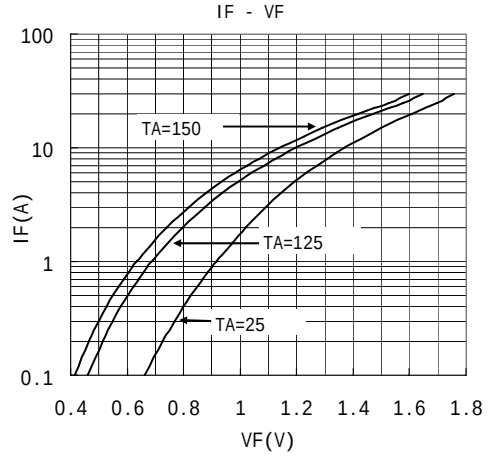
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
Working Peak Reverse Voltage	V_{RMS}	420	V
Average Rectified Forward Current	I_F	8	A
Non Repetitive Peak Surge Current	I_{FSM}	125	A
Thermal resistance, junction to case	R_{Jc}	3.5	/W
Junction and Storage Temperature Range	T_j T_{stg}	-55 150	

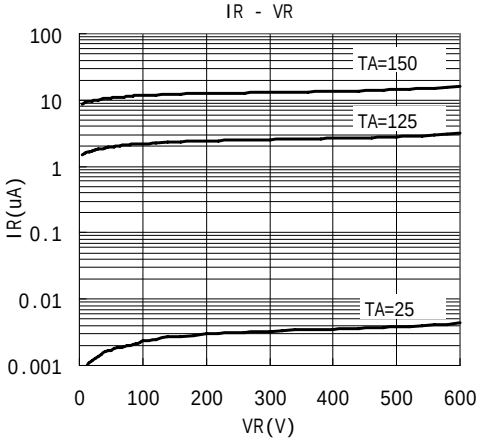
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_{BR}	I_R=100uA	600			V
		I_F=8A Tc=25		1.4	1.7	V
Forward Voltage	V_F	I_F=16A Tc=25		1.7	2.1	V
1.4 1.7		I=16A Tc1=25				

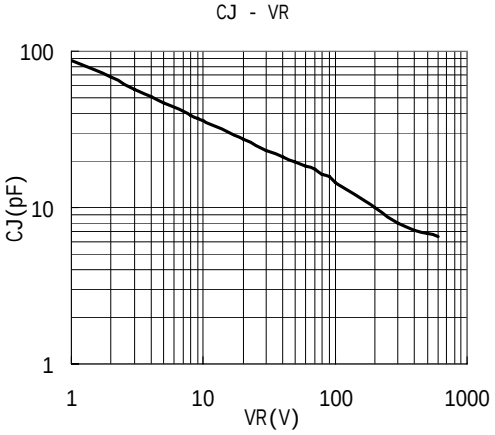
/ Electrical Characteristic Curve



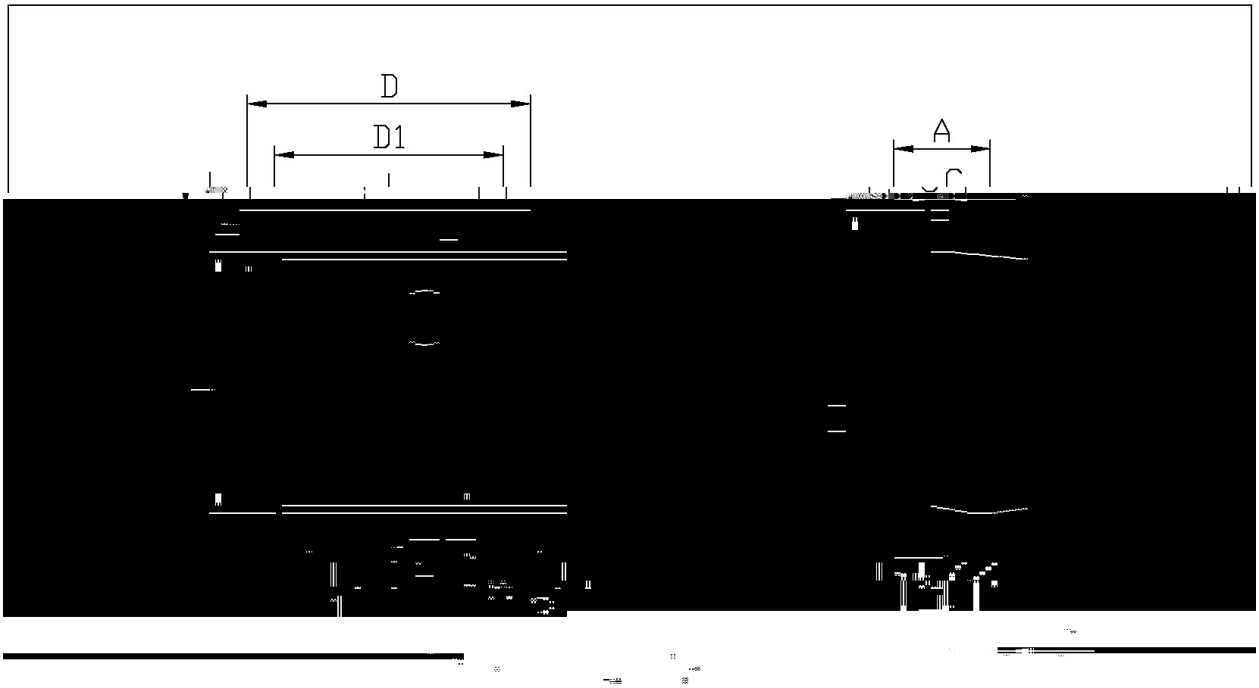








/ Package Dimensions



00	0.10	D1	5.10	5.50	K	0.

TO-252

/ Marking Instructions



BR

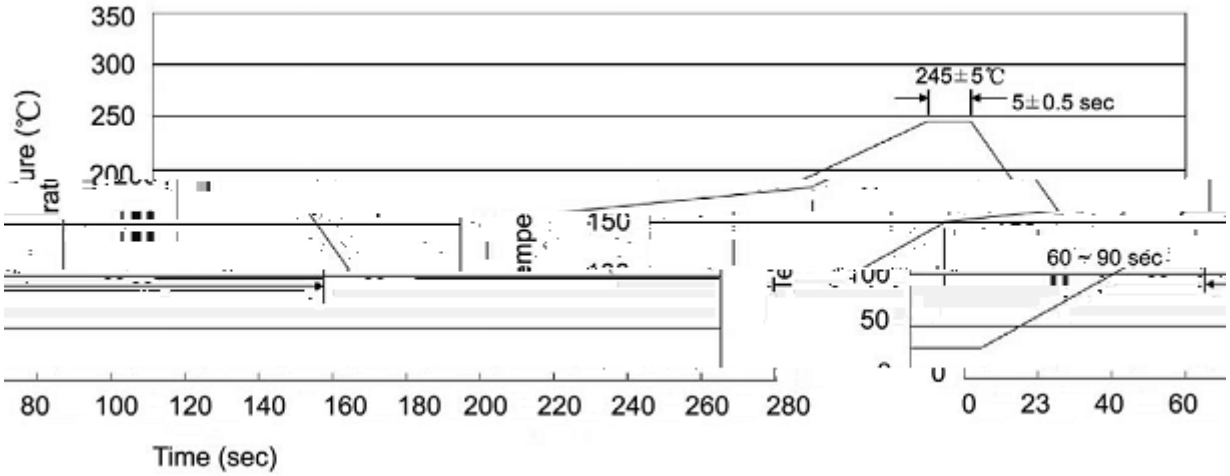
MUR860

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Note:

BR:	Company Code
MUR860	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



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